

2SC1317, 2SC1318

Silicon NPN epitaxial planar type

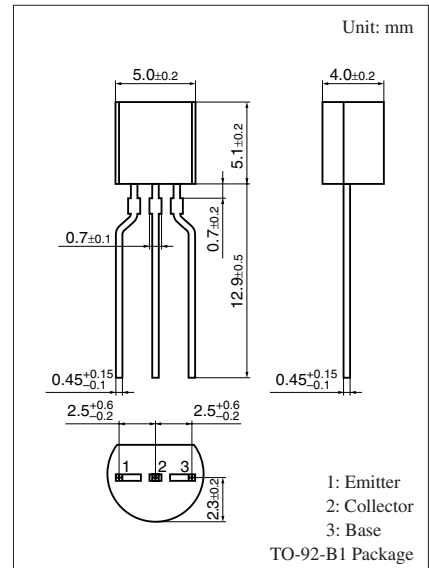
For low-frequency power amplification and driver amplification
Complementary to 2SA0719 and 2SA0720

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Complementary pair with 2SA0719 and 2SA0720

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SC1317	30	V
	2SC1318	60	
Collector-emitter voltage (Base open)	2SC1317	25	V
	2SC1318	50	
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Collector current	I_C	0.5	A
Peak collector current	I_{CP}	1	A
Collector power dissipation	P_C	625	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

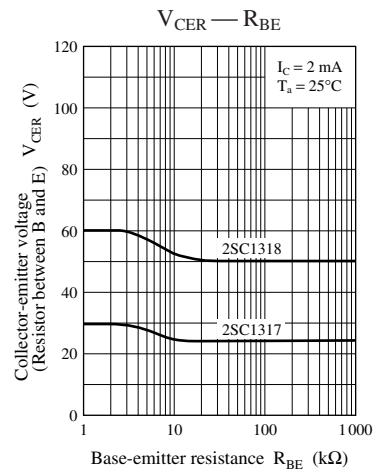
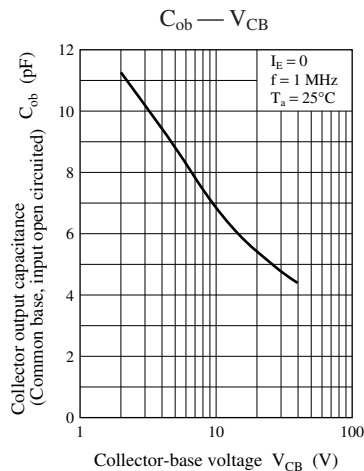
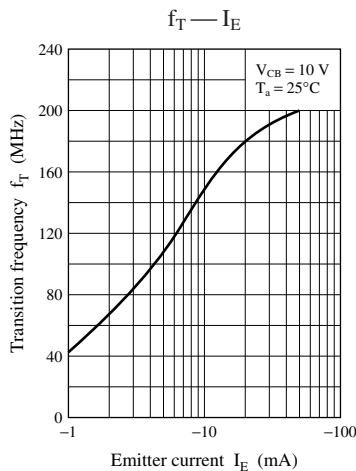
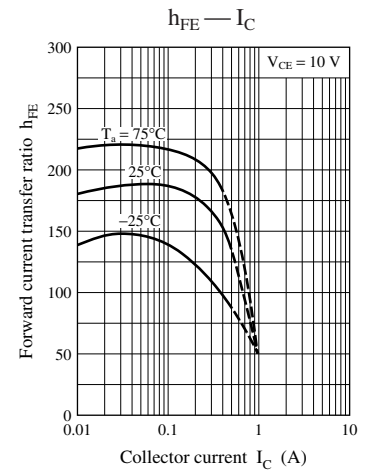
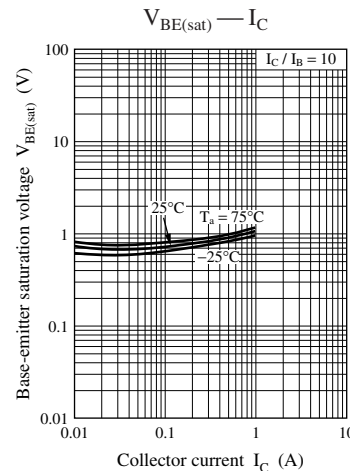
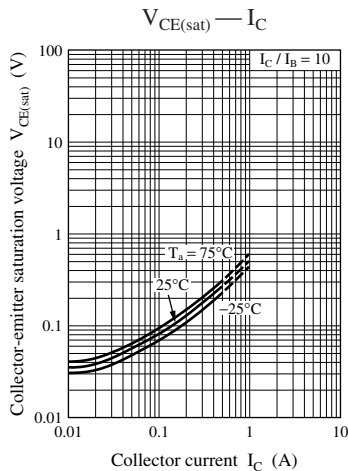
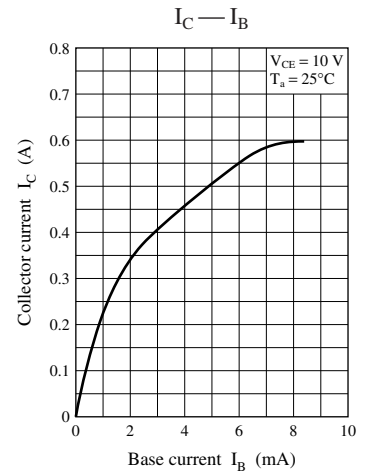
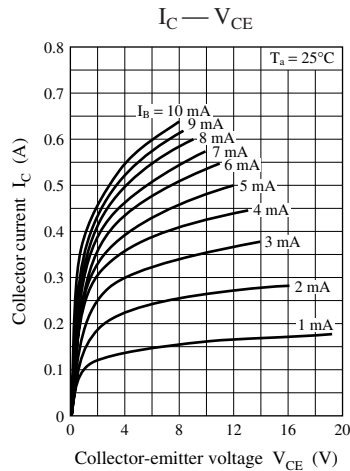
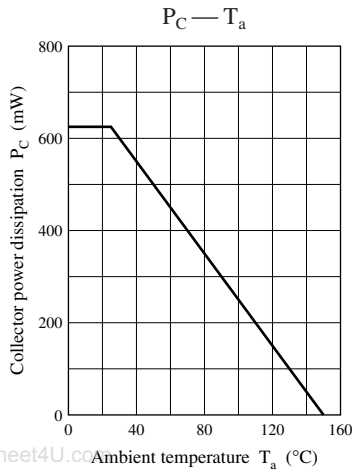
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	2SC1317	$I_C = 10 \mu\text{A}, I_E = 0$	30			V
	2SC1318		60			
Collector-emitter voltage (Base open)	2SC1317	$I_C = 10 \text{mA}, I_B = 0$	25			V
	2SC1318		50			
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{V}, I_E = 0$			0.1	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = 10 \text{V}, I_C = 150 \text{mA}$	85		340	—
	h_{FE2}	$V_{CE} = 10 \text{V}, I_C = 500 \text{mA}$	40			—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$		0.35	0.60	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$		1.1	1.5	V
Transition frequency	f_T	$V_{CB} = 10 \text{V}, I_E = -50 \text{mA}, f = 200 \text{MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{V}, I_E = 0, f = 1 \text{MHz}$		6	15	pF

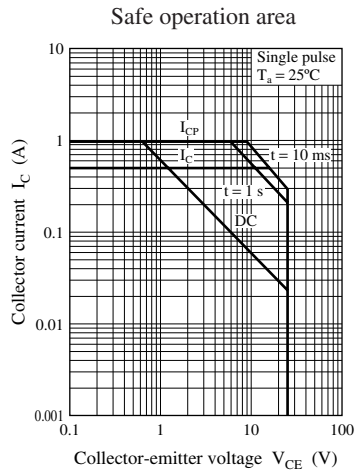
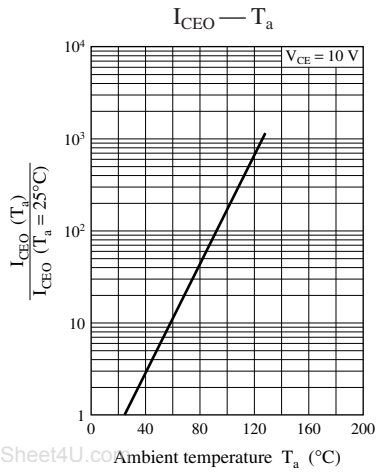
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R	S
h_{FE1}	85 to 170	120 to 240	170 to 340





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